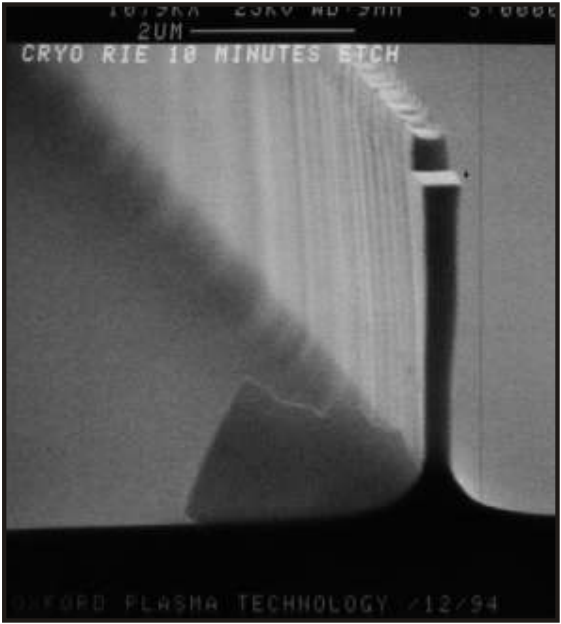
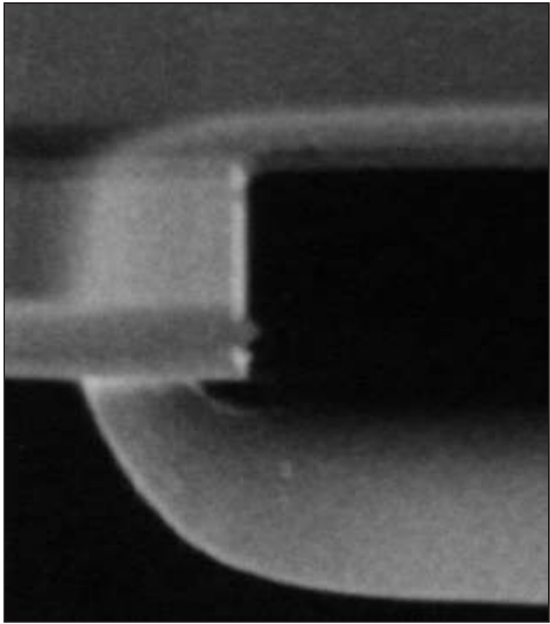


Plasmalab Data

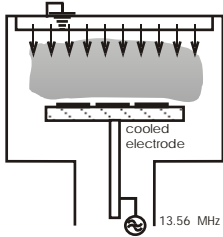
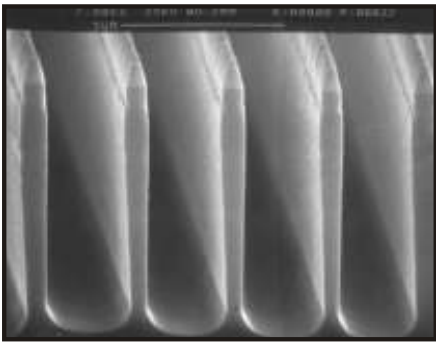
Cryo cooling: Deep Si Etching (RIE)



SF₆ process at -70 °C



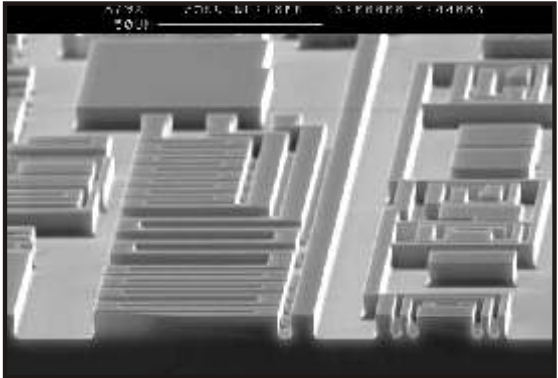
SF₆ process at +10 °C



- Plasmalab 80 Plus*
- Plasmalab 800 Plus*
- Plasmalab System 100*
- Plasmalab System 133*



Technology:
Parallel Plate Configuration
RIE Mode (13.56 MHz)
Cryo Cooled Table: -150 - +400 °C
Thermal Contact: Helium



Results:
etch rate ~0.3µm/min (dependent on Si area)
etch rate uniformity < ± 4% (100 mm wafer)
selectivity to positive photoresist >3-6:1
(dependent on resist type)
selectivity to silicon dioxide ~5-10:1
undercut ~0%
profile 87-90°